# BUK98180-100A

## N-channel TrenchMOS logic level FET

**Rev. 03 — 3 June 2010** **Product data sheet**

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

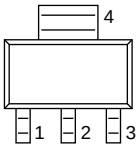
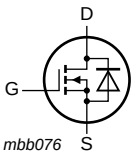
### 1.4 Quick reference data

**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | $T_j \geq 25$ °C; $T_j \leq 150$ °C | - | - | 100 | V |
| $I_D$ | drain current | $V_{GS} = 5$ V; $T_{sp} = 25$ °C; see Figure 1; see Figure 3 | - | - | 4.6 | A |
| $P_{tot}$ | total power dissipation | $T_{sp} = 25$ °C; see Figure 2 | - | - | 8 | W |
| **Static characteristics** | | | | | | |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS} = 10$ V; $I_D = 5$ A; $T_j = 25$ °C | - | 147 | 173 | mΩ |
| | | $V_{GS} = 4.5$ V; $I_D = 5$ A; $T_j = 25$ °C | - | - | 201 | mΩ |
| | | $V_{GS} = 5$ V; $I_D = 5$ A; $T_j = 25$ °C; see Figure 12; see Figure 13 | - | 153 | 180 | mΩ |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 4$ A; $V_{sup} \leq 100$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped | - | - | 16 | mJ |

## 2. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | G | gate |  |  |
| 2 | D | drain | | |
| 3 | S | source | | |
| 4 | D | drain | | |



**SOT223 (SC-73)**



## 3. Ordering information

**Table 3. Ordering information**

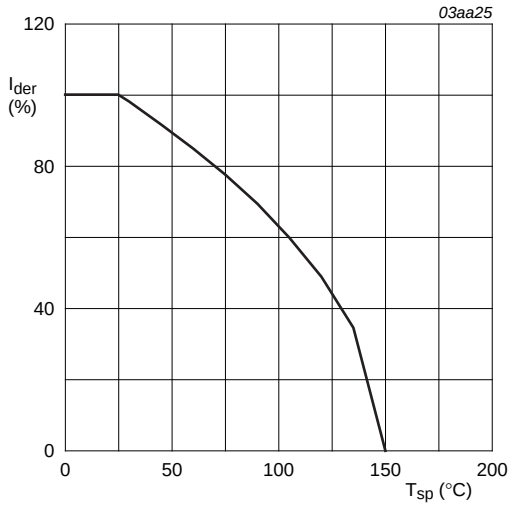
| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| BUK98180-100A | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 |

## 4. Limiting values

**Table 4. Limiting values**

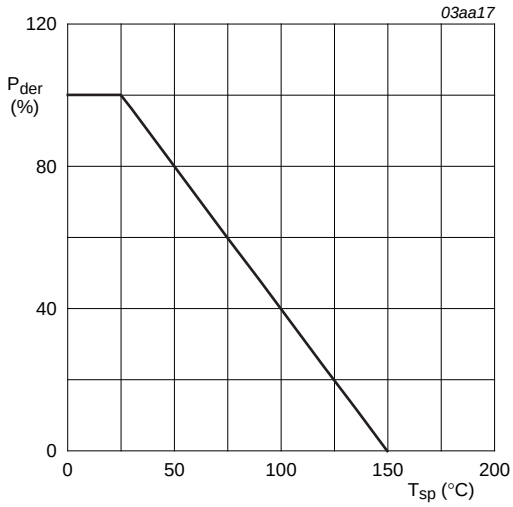
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | $T_j \geq 25$ °C; $T_j \leq 150$ °C | - | - | 100 | V |
| $V_{DGR}$ | drain-gate voltage | $R_{GS}$ = 20 kΩ | - | - | 100 | V |
| $V_{GS}$ | gate-source voltage | | -10 | - | 10 | V |
| $I_D$ | drain current | $T_{sp}$ = 25 °C; $V_{GS}$ = 5 V; see Figure 1; see Figure 3 | - | - | 4.6 | A |
| | | $T_{sp}$ = 100 °C; $V_{GS}$ = 5 V; see Figure 1 | - | - | 3 | A |
| $I_{DM}$ | peak drain current | $T_{sp}$ = 25 °C; $t_p \leq 10$ µs; pulsed; see Figure 3 | - | - | 18 | A |
| $P_{tot}$ | total power dissipation | $T_{sp}$ = 25 °C; see Figure 2 | - | - | 8 | W |
| $T_{stg}$ | storage temperature | | -55 | - | 150 | °C |
| $T_j$ | junction temperature | | -55 | - | 150 | °C |
| $V_{GSM}$ | peak gate-source voltage | pulsed; $t_p \leq 50$ µs | -15 | - | 15 | V |
| **Source-drain diode** | | | | | | |
| $I_S$ | source current | $T_{sp}$ = 25 °C | - | - | 4.6 | A |
| $I_{SM}$ | peak source current | $t_p \leq 10$ µs; pulsed; $T_{sp}$ = 25 °C | - | - | 18 | A |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D$ = 4 A; $V_{sup} \leq 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped | - | - | 16 | mJ |



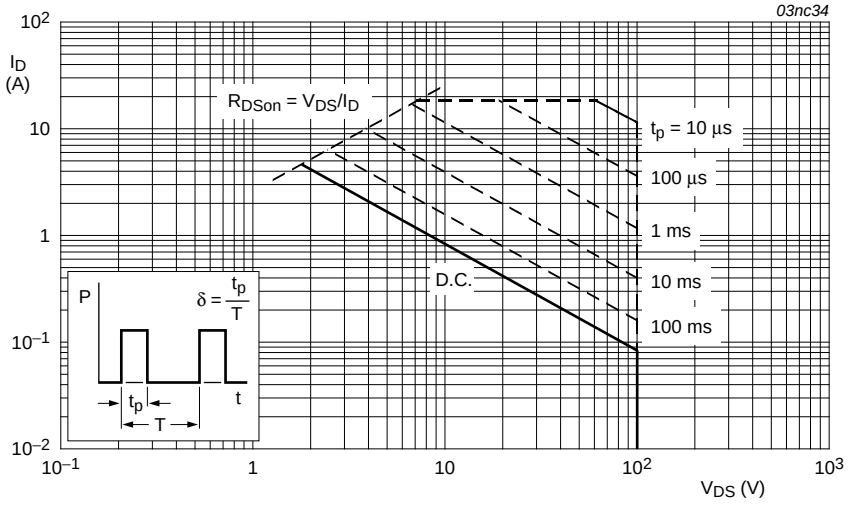

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

**Fig 1. Normalized continuous drain current as a function of solder point temperature**




$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

**Fig 2. Normalized total power dissipation as a function of solder point temperature**




$T_{amb} = 25°C; I_{DM}$ is single pulse

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | see Figure 4 | - | - | 15 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | | - | 70 | - | K/W |

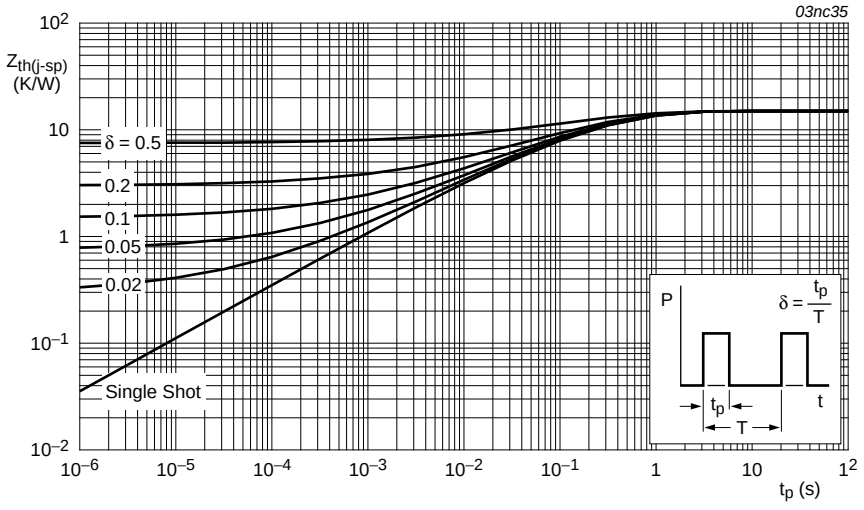
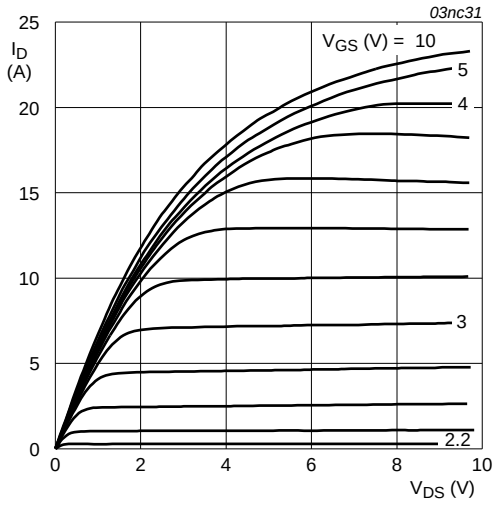



**Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration**

# 6. Characteristics

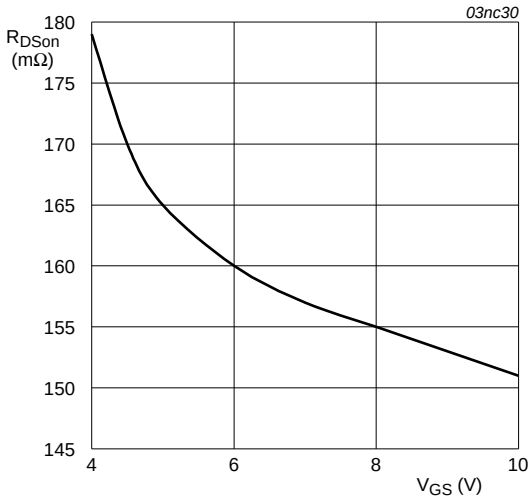
**Table 6. Characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C | 100 | - | - | V |
| | | $I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C | 89 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 25 °C; see Figure 11 | 1 | 1.5 | 2 | V |
| | | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = -55 °C; see Figure 11 | - | - | 2.3 | V |
| | | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 150 °C; see Figure 11 | 0.6 | - | - | V |
| $I_{DSS}$ | drain leakage current | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C | - | - | 500 | µA |
| | | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C | - | 0.05 | 10 | µA |
| $I_{GSS}$ | gate leakage current | $V_{DS}$ = 0 V; $V_{GS}$ = 10 V; $T_j$ = 25 °C | - | 2 | 100 | nA |
| | | $V_{DS}$ = 0 V; $V_{GS}$ = -10 V; $T_j$ = 25 °C | - | 2 | 100 | nA |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 5 A; $T_j$ = 25 °C | - | 147 | 173 | mΩ |
| | | $V_{GS}$ = 4.5 V; $I_D$ = 5 A; $T_j$ = 25 °C | - | - | 201 | mΩ |
| | | $V_{GS}$ = 5 V; $I_D$ = 5 A; $T_j$ = 25 °C; see Figure 12; see Figure 13 | - | 153 | 180 | mΩ |
| | | $V_{GS}$ = 5 V; $I_D$ = 5 A; $T_j$ = 150 °C; see Figure 12; see Figure 13 | - | - | 389 | mΩ |
| **Dynamic characteristics** | | | | | | |
| $C_{iss}$ | input capacitance | $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz; $T_j$ = 25 °C; see Figure 14 | - | 464 | 619 | pF |
| $C_{oss}$ | output capacitance | | - | 60 | 72 | pF |
| $C_{rss}$ | reverse transfer capacitance | | - | 36 | 50 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS}$ = 30 V; $R_L$ = 1.2 Ω; $V_{GS}$ = 5 V; $R_{G(ext)}$ = 10 Ω; $T_j$ = 25 °C | - | 7 | - | ns |
| $t_r$ | rise time | | - | 89 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 18 | - | ns |
| $t_f$ | fall time | | - | 25 | - | ns |
| **Source-drain diode** | | | | | | |
| $V_{SD}$ | source-drain voltage | $I_S$ = 5 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see Figure 15 | - | 0.85 | 1.2 | V |
| $t_{rr}$ | reverse recovery time | $I_S$ = 20 A; $dI_S/dt$ = -100 A/µs; $V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C | - | 49 | - | ns |
| $Q_r$ | recovered charge | | - | 130 | - | nC |



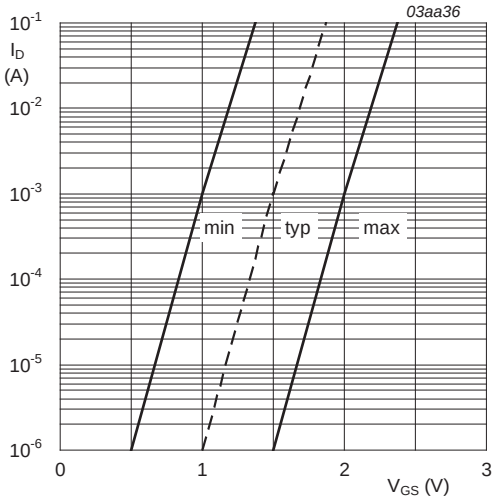

$T_j = 25°C$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



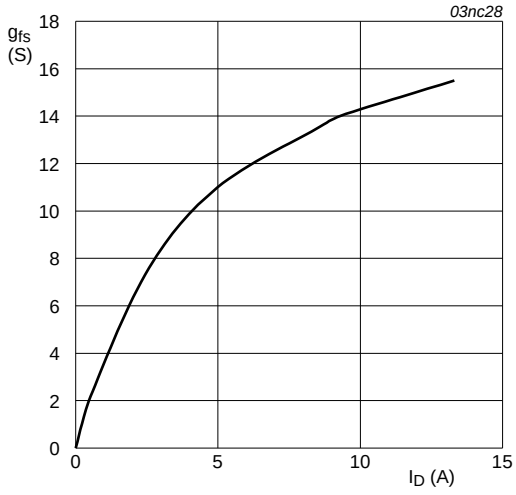

$T_j = 25°C; I_D = 5A$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values**



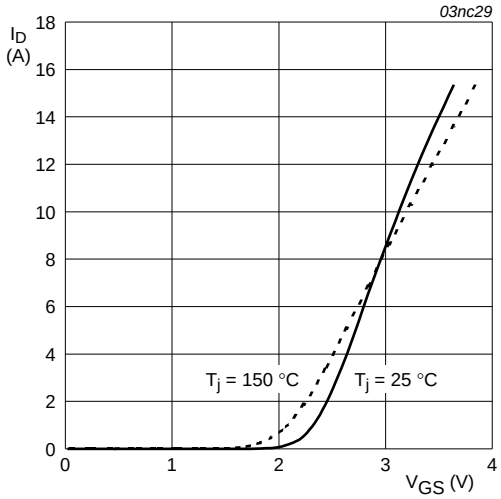

$T_j = 25°C; V_{DS} = V_{GS}$

**Fig 7. Sub-threshold drain current as a function of gate-source voltage**



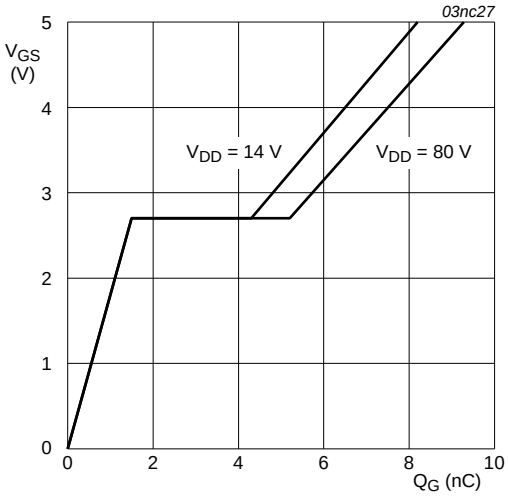

$T_j = 25°C; V_{DS} = 25V$

**Fig 8. Forward transconductance as a function of drain current; typical values**



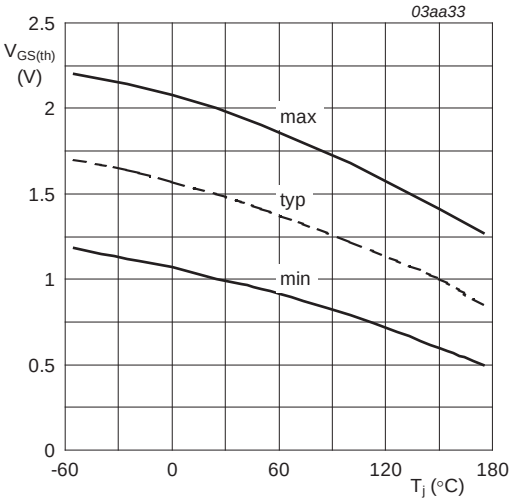

$V_{DS} = 25V$

**Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



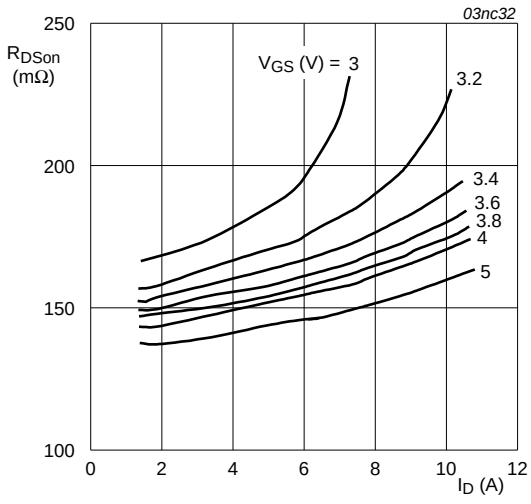

$T_j = 25°C; I_D = 5A$

**Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values**



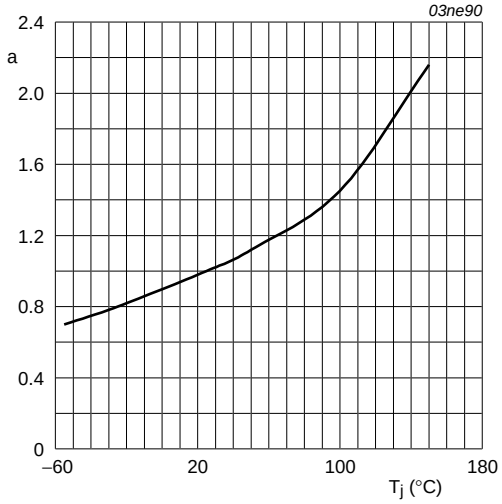

$I_D = 1mA; V_{DS} = V_{GS}$

**Fig 11. Gate-source threshold voltage as a function of junction temperature**



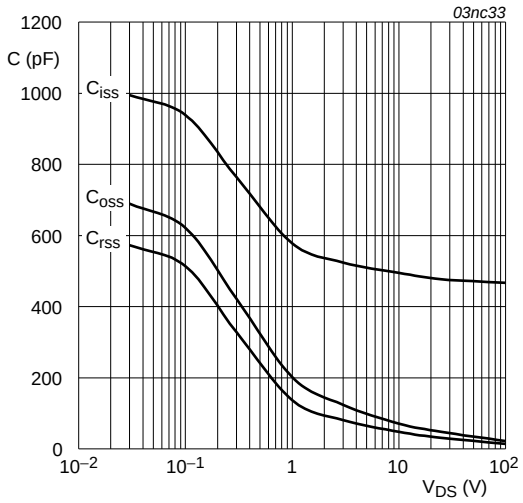

$T_j = 25°C$

**Fig 12. Drain-source on-state resistance as a function of drain current; typical values**



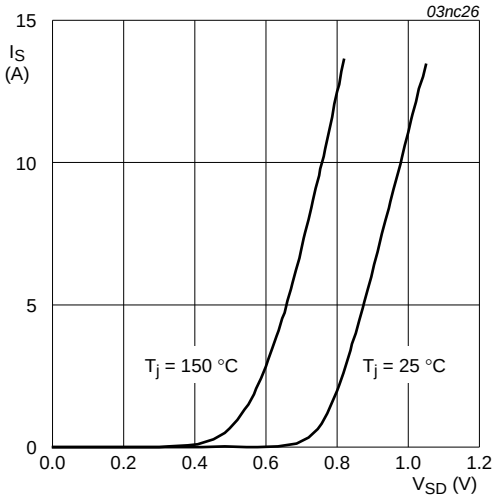

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**




$$V_{GS} = 0V; f = 1MHz$$

**Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

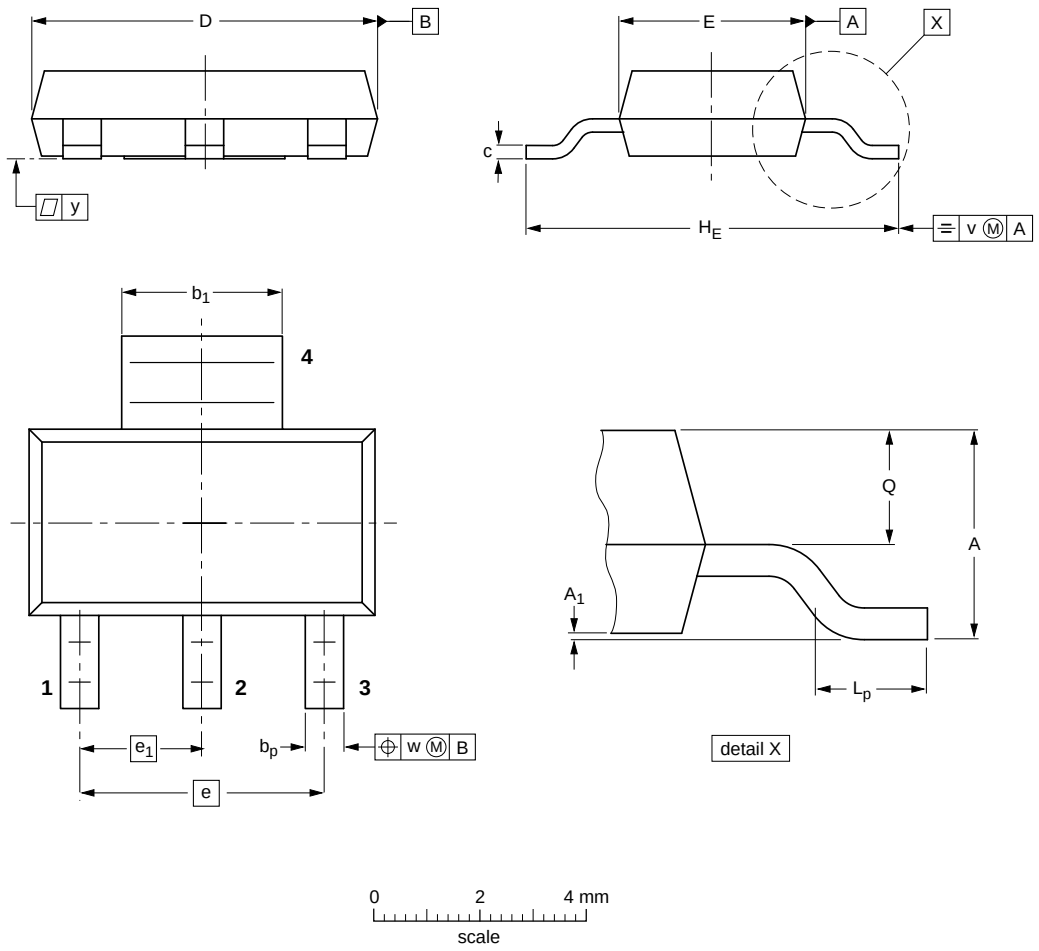



$$V_{GS} = 0V$$

**Fig 15. Reverse diode current as a function of reverse diode voltage; typical values**

## 7. Package outline

**Plastic surface-mounted package with increased heatsink; 4 leads** **SOT223**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A | $A_1$ | $b_p$ | $b_1$ | c | D | E | e | $e_1$ | $H_E$ | $L_p$ | Q | v | w | y |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 1.8<br>1.5 | 0.10<br>0.01 | 0.80<br>0.60 | 3.1<br>2.9 | 0.32<br>0.22 | 6.7<br>6.3 | 3.7<br>3.3 | 4.6 | 2.3 | 7.3<br>6.7 | 1.1<br>0.7 | 0.95<br>0.85 | 0.2 | 0.1 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT223 | | | SC-73 | | | ~~04-11-10~~<br>06-03-16 |

**Fig 16. Package outline SOT223 (SC-73)**

## 8. Revision history

**Table 7. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| BUK98180-100A v.3 | 20100603 | Product data sheet | - | BUK98180-100A-02 |
| Modifications: | • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.<br>• Legal texts have been adapted to the new company name where appropriate. | | | |
| BUK98180-100A-02 (9397 750 08277) | 20010518 | Product data | - | - |

# 9. Legal information

## 9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 11. Contents





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